

A03404A

N-Channel Enhancement Mode Field Effect Transistor

General Description

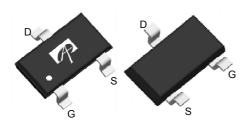
The AO3404A uses advanced trench technology to provide excellent $R_{\rm DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

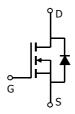
Features

$$\begin{split} &V_{DS}\left(V\right) = 30V \\ &I_{D} = 5.8A & (V_{GS} = 10V) \\ &R_{DS(ON)} < 25m\Omega & (V_{GS} = 10V) \\ &R_{DS(ON)} < 35m\Omega & (V_{GS} = 4.5V) \end{split}$$



SOT23
Top View Bottom View





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units		
Drain-Source Voltage		V _{DS}	30	V		
Gate-Source Voltage		V_{GS}	±20	V		
Continuous Drain	T _A =25°C		5.8			
Current A,F	T _A =70°C	I _D	4.9	A		
Pulsed Drain Current ^B		I _{DM}	64			
	T _A =25°C	В	1.4	10/		
Power Dissipation	T _A =70°C	$-P_D$	0.9	W		
Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C		

Thermal Characteristics								
Parameter	Symbol Typ Max			Units				
Maximum Junction-to-Ambient A	t ≤ 10s	$-R_{\theta JA}$	65	90	°C/W			
Maximum Junction-to-Ambient A	Steady-State	Steady-State		125	°C/W			
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	63	80	°C/W			



Electrical Characteristics (T_.=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Units				
STATIC PARAMETERS										
BV _{DSS}	Drain-Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30			V				
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V			1	μА				
		T _J =55°C			5	μ				
I_{GSS}	Gate-Body leakage current	V_{DS} =0V, V_{GS} = ±20V			100	nA				
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS} I_{D}=250\mu A$	1.5	2.1	2.6	V				
$I_{D(ON)}$	On state drain current	V _{GS} =4.5V, V _{DS} =5V	64			Α				
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =5.8A		18.4	25	mΩ				
		T _J =125°C		26.2	36	11122				
		V _{GS} =4.5V, I _D =4.8A		24.5	35	mΩ				
g _{FS}	Forward Transconductance	V_{DS} =5V, I_D =5.8A		22		S				
V_{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.75	1	V				
I_S	Maximum Body-Diode Continuous Current				2.5	Α				
DYNAMIC	PARAMETERS	•		•	•					
C _{iss}	Input Capacitance			373	448	pF				
C _{oss}	Output Capacitance	V_{GS} =0V, V_{DS} =15V, f=1MHz		67		pF				
C_{rss}	Reverse Transfer Capacitance			41		pF				
R_g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.9	1.8	2.8	Ω				
SWITCHI	NG PARAMETERS									
Q _g (10V)	Total Gate Charge			7.1	11	nC				
Q _g (4.5V)	Total Gate Charge	VGS=10V, VDS=15V, ID=5.8A		3.3		nC				
Q_{gs}	Gate Source Charge	7 VGS-10V, VDS-15V, ID-5.6A		1.4		nC				
Q_{gd}	Gate Drain Charge]		1.7		nC				
t _{D(on)}	Turn-On DelayTime			4.5	6.5	ns				
t _r	Turn-On Rise Time	V_{GS} =10V, V_{DS} =15V, R_L =2.6 Ω ,		2.4		ns				
t _{D(off)}	Turn-Off DelayTime	R_{GEN} =3 Ω		14.8		ns				
t _f	Turn-Off Fall Time]		2.5		ns				
t _{rr}	Body Diode Reverse Recovery Time	I _F =5.8A, di/dt=100A/μs		10.5	12.6	ns				
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =5.8A, di/dt=100A/μs		4.5		nC				

A: The value of R $_{\text{BJA}}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T $_{\text{A}}$ =25 $^{\circ}$ C. The value in any given application depends on the user's specific board design. The current rating is based on the t $^{\circ}$ 10s thermal resistance rating. B: Repetitive rating, pulse width limited by junction temperature.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

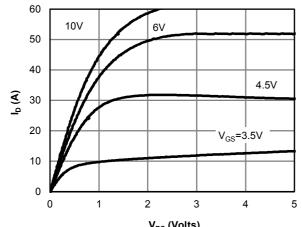
D. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25 $^{\circ}$ C. The SOA curve provides a single pulse rating.

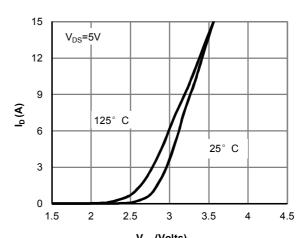
F.The current rating is based on the t≤ 10s thermal resistance rating.



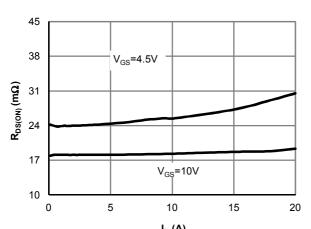
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



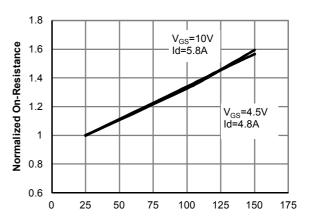
V_{DS} (Volts) Figure 1: On-Region Characteristics



V_{GS} (Volts) Figure 2: Transfer Characteristics



I_D (A)
Figure 3: On-Resistance vs. Drain Current and
Gate Voltage



Temperature (°C)
Figure 4: On-Resistance vs. Junction Temperature

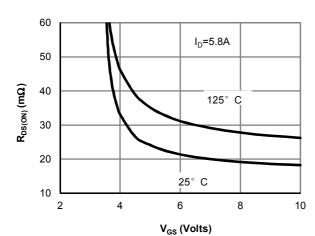
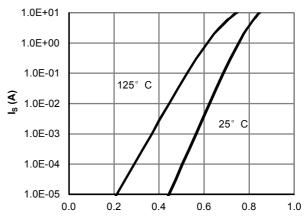


Figure 5: On-Resistance vs. Gate-Source Voltage



V_{SD} (Volts) Figure 6: Body-Diode Characteristics



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

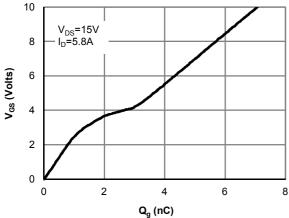


Figure 7: Gate-Charge Characteristics

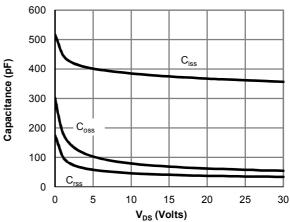


Figure 8: Capacitance Characteristics

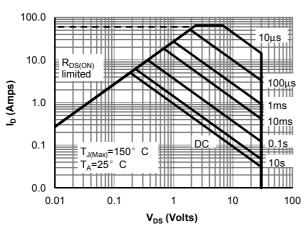


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

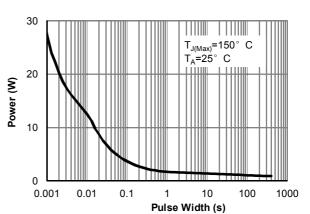
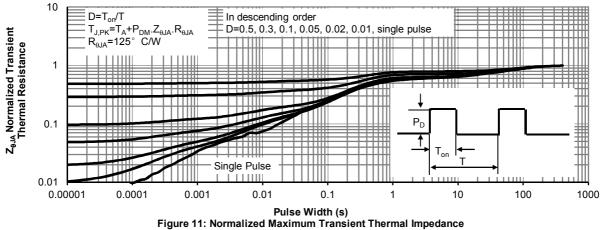


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)



Rev.5.0: June 2015 www.aosmd.com Page 4 of 4

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Alpha & Omega manufacturer:

Other Similar products are found below:

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3